

11N40

Power MOSFET

400 V N-CHANNEL MOSFET

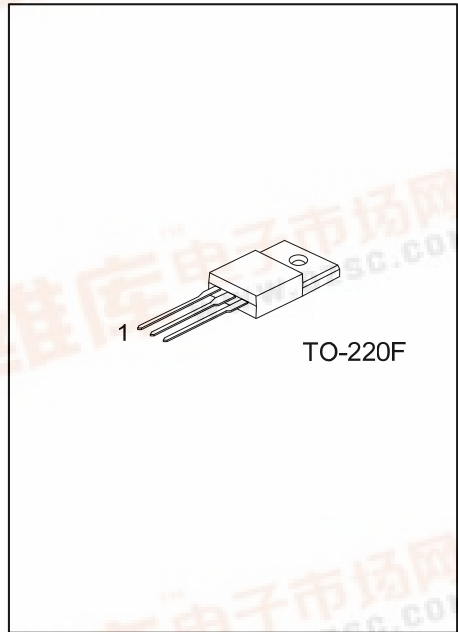
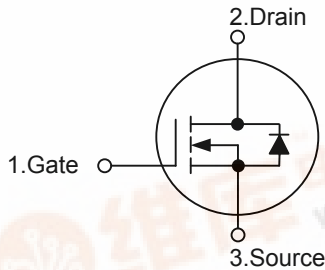
DESCRIPTION

The **11N40** uses UTC's advanced proprietary, planar stripe, DMOS technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with low gate voltages. This device is suitable for use as a load switch or in PWM applications.

FEATURES

- * $R_{DS(ON)} = 0.48\Omega @ V_{GS} = 10 V$
- * Ultra low gate charge (typical 27 nC)
- * Low reverse transfer capacitance ($C_{RSS} =$ typical 20 pF)
- * Fast switching capability
- * Avalanche energy specified
- * Improved dv/dt capability, high ruggedness

SYMBOL



Lead-free: 11N40L
Halogen-free: 11N40G

ORDERING INFORMATION

Ordering Number			Package	Pin Assignment			Packing
Normal	Lead Free Plating	Halogen Free		1	2	3	
11N40-TF3-T	11N40L-TF3-T	11N40G-TF3-T	TO-220F	G	D	S	Tube

<p>11N40L-TF3-T</p> <p>(1)Packing Type</p> <p>(2)Package Type</p> <p>(3)Lead Plating</p>	<p>(1) T: Tube</p> <p>(2) TF3: TO-220F</p> <p>(3) G: Halogen Free, L: Lead Free, Blank: Pb/Sn</p>
------------------------------------------------------------------------------------------	---------------------------------------------------------------------------------------------------

■ ABSOLUTE MAXIMUM RATING ($T_C = 25^\circ\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	400	V
Gate-Source Voltage		V_{GSS}	± 30	V
Continuous Drain Current ($T_C = 25^\circ\text{C}$)		I_D	11.4	A
Pulsed Drain Current (Note 1)		I_{DM}	46	A
Avalanche Current (Note 1)		I_{AR}	11.4	A
Avalanche Energy	Single Pulsed(Note 2)	E_{AS}	520	mJ
	Repetitive(Note 1)	E_{AR}	14.7	
Peak Diode Recovery dv/dt (Note 3)		dv/dt	4.5	V/ns
Power Dissipation Derate above 25°C		P_D	147 1.18	W W/ $^\circ\text{C}$
Junction Temperature		T_J	150	$^\circ\text{C}$
Storage Temperature		T_{STG}	-55 ~ +150	$^\circ\text{C}$

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged.
Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ THERMAL DATA

PARAMETER	SYMBOL	MIN	TYP	MAX	UNIT
Junction-to- Ambient	θ_{JA}			62.5	$^\circ\text{C}/\text{W}$
Junction-to-Case	θ_{JC}			0.85	$^\circ\text{C}/\text{W}$

■ ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	400			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 400\text{V}, V_{GS} = 0\text{ V}$			1	μA
		$V_{DS} = 320\text{V}, T_C = 125^\circ\text{C}$			10	
Gate-Body Leakage Current	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 30\text{ V}$			± 100	nA
Breakdown Voltage Temperature Coefficient	$\Delta BV_{DSS}/\Delta T_J$	$I_D = 250\ \mu\text{A}$, Referenced to 25°C		0.42		mV/ $^\circ\text{C}$
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	2.0		4.0	V
Static Drain-Source On-Resistance	$R_{DS(ON)}$	$V_{GS} = 10\text{ V}, I_D = 5.7\text{ A}$		0.38	0.48	Ω
DYNAMIC PARAMETERS						
Input Capacitance	C_{ISS}	$V_{DS} = 25\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$		1100	1400	pF
Output Capacitance	C_{OSS}		180	240		
Reverse Transfer Capacitance	C_{RSS}		20	30		
SWITCHING PARAMETERS						
Turn-ON Delay Time	$t_{D(ON)}$	$V_{DD} = 200\text{V}, I_D = 11.4\text{A}, R_{GEN} = 25\Omega$ (Note 4,5)		30	70	ns
Turn-ON Rise Time	t_R		100	210		
Turn-OFF Delay Time	$t_{D(OFF)}$		60	130		
Turn-OFF Fall-Time	t_F		60	130		
Total Gate Charge	Q_G	$V_{DS} = 320\text{V}, V_{GS} = 10\text{V}, I_D = 11.4\text{A}$ (Note 4,5)		27	35	nC
Gate Source Charge	Q_{GS}		7.3			
Gate Drain Charge	Q_{GD}		12.3			

■ ELECTRICAL CHARACTERISTICS(Cont.)

SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS						
Drain-Source Diode Forward Voltage	V_{SD}	$I_S=11.4\text{ A}, V_{GS}=0\text{V}$			1.5	V
Maximum Continuous Drain-Source Diode Forward Current	I_S				11.4	A
Maximum Pulsed Drain-Source Diode Forward Current	I_{SM}				46	
Reverse Recovery Time	t_{RR}	$V_{GS} = 0\text{ V}, di_F/dt = 100\text{ A/s},$		240		ns
Reverse Recovery Charge	Q_{RR}	$I_S = 11.4\text{ A (Note 4)}$		1.8		μC

- Note
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
 2. $L=7\text{mH}, I_{AS}=11.4\text{A}, V_{DD}=50\text{V}, R_G=25\Omega,$ Satarting $T_J=25^\circ\text{C}.$
 3. $I_{SD} \leq 11.4\text{A}, di/dt \leq 200\text{A}/\mu\text{s}, V_{DD} \leq BV_{DSS},$ Satarting $T_J=25^\circ\text{C}.$
 4. Pulse Test: Pulse Width $\leq 300\text{ s},$ Duty Cycle $\leq 2\%.$
 5. Independent of operating temperature.

■ TEST CIRCUIT

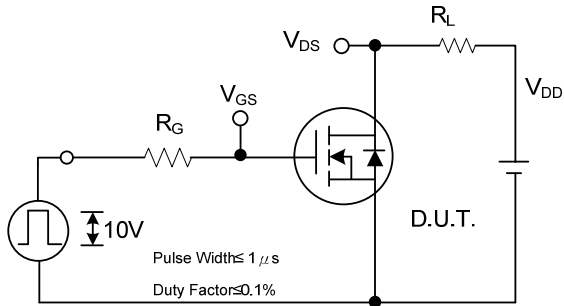


Fig. 2A Switching Test Circuit

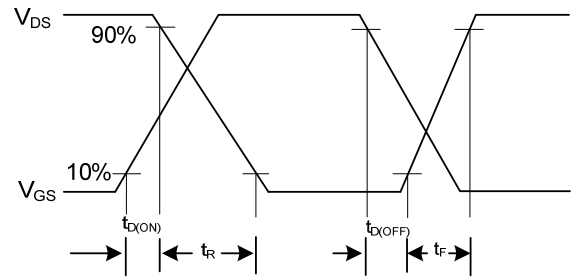


Fig. 2B Switching Waveforms

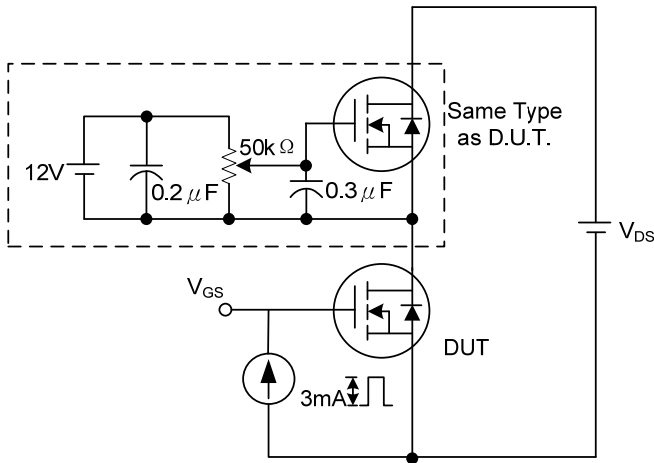


Fig. 3A Gate Charge Test Circuit

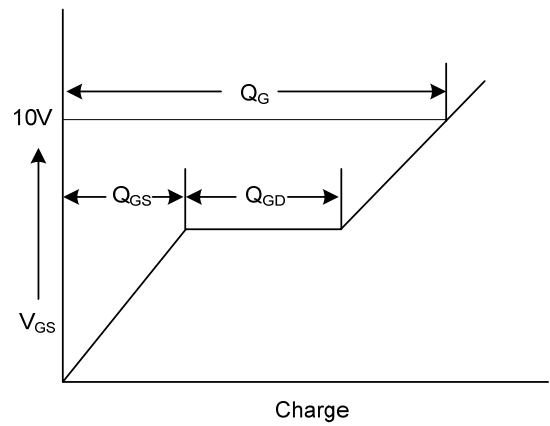


Fig. 3B Gate Charge Waveform

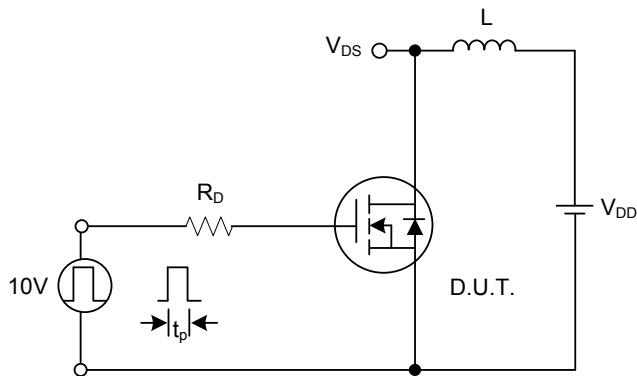


Fig. 4A Unclamped Inductive Switching Test Circuit

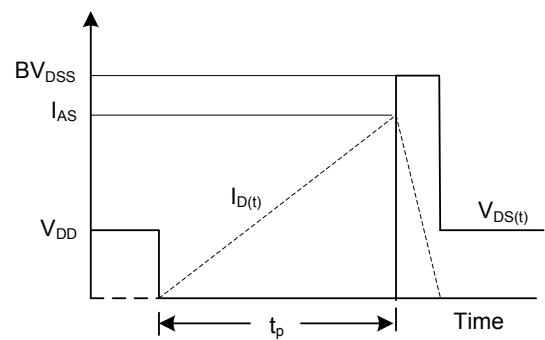


Fig. 4B Unclamped Inductive Switching Waveforms

■ TEST CIRCUIT(Cont.)

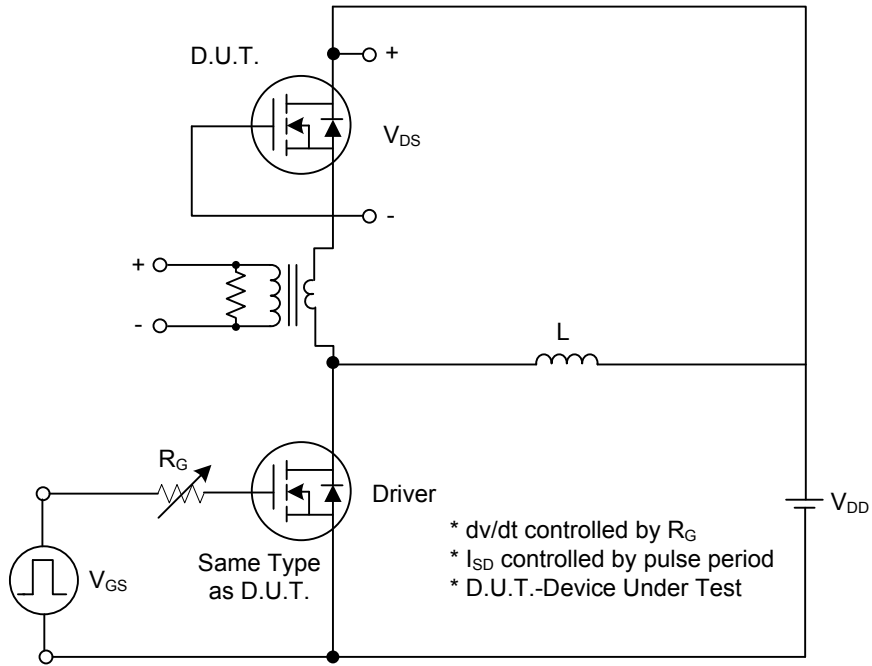
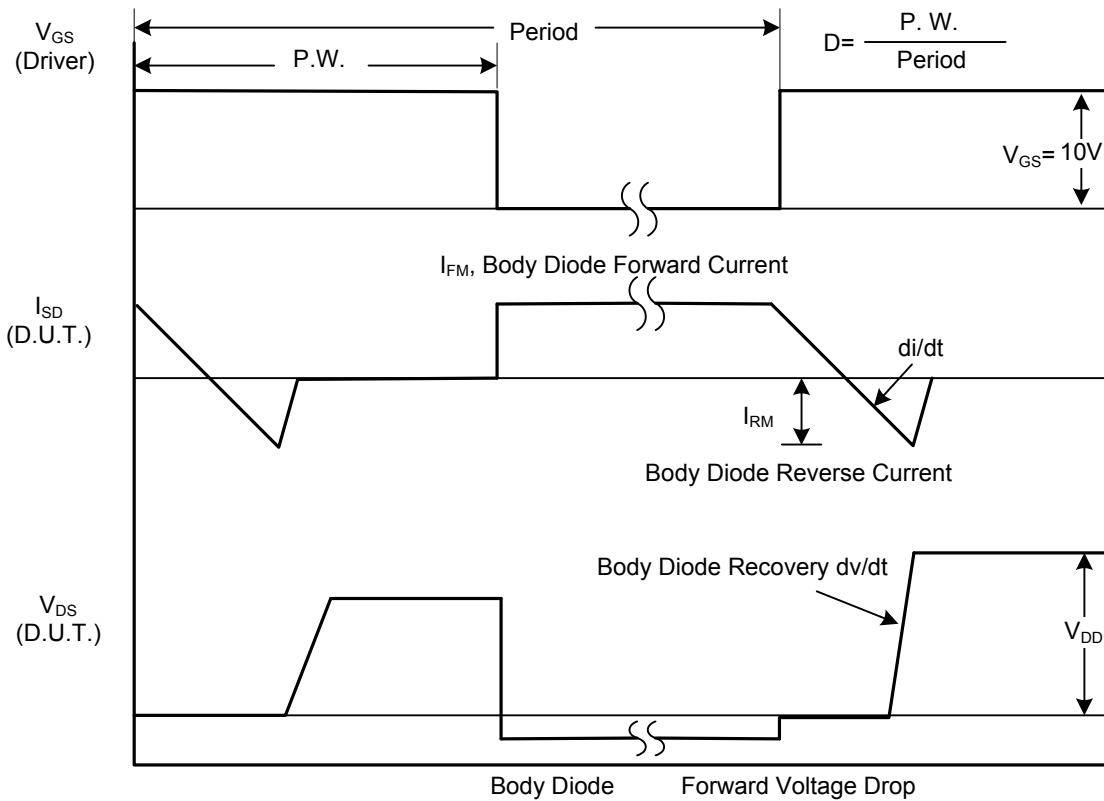


Fig. 1A Peak Diode Recovery dv/dt Test Circuit



UTC assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all UTC products described or contained herein. UTC products are not designed for use in life support appliances, devices or systems where malfunction of these products can be reasonably expected to result in personal injury. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner. The information presented in this document does not form part of any quotation or contract, is believed to be accurate and reliable and may be changed without notice.